

G.R. No.

**DECEMBER 2017 / ENDSEM****F. Y. B. TECH. (COMMON) (SEMESTER - I)****COURSE NAME: ENGINEERING PHYSICS****COURSE CODE: ES10175A****(2017 PATTERN)**

Time: [2 Hours]

[Max. Marks: 50]

**Instructions to candidates:**

- 1) Answer Q.1 OR Q.2, Q.3 OR Q.4 and Q.5
- 2) Figures to the right indicate full marks.
- 3) Use of scientific calculator is allowed
- 4) Use suitable data wherever required

- Q1 a) Explain with the help of neat diagrams construction and working of CO<sub>2</sub> laser. [6]
- b) Derive an expression for Natural Aperture (NA) of an optical fibre. [6]
- c) Laser beam comes out of a diode laser ( $\lambda = 8732\text{\AA}$ ) through a rectangular slit with width 1mm. Calculate the width of the beam at a distance of 100m from the source. [4]

**OR**

- Q2 a) Describe with the help of neat diagrams, construction and working of a Single Hetero-junction diode laser. [6]
- b) Explain, with the help of appropriate diagrams, the role of optical cavity in directionality, monochromaticity and coherence of a laser. [6]
- c) Population inversion is obtained in a CO<sub>2</sub> laser. The ratio of number of molecules in the higher energy state to that in the lowest energy state  $\left(\frac{N_2}{N_1}\right)$  is 1.5. Calculate the equivalent temperature for laser wavelength  $\lambda = 9.6\text{ }\mu\text{m}$ . Given, Boltzmann constant  $k = 1.38 \times 10^{-23}\text{ J/K}$ . [4]
- Q3 a) Draw a neat diagram of a nuclear fission reactor and explain its construction and working. [6]
- b) With the help of a potential energy diagram, explain fission on the basis of liquid drop model. [4]
- c) Calculate the energy of the ground state of a neutron trapped in an infinite potential well of width  $L = 10^{-14}\text{ m}$ . Given mass of

neutron =  $1.67 \times 10^{-27}$  kg,  $h = 6.63 \times 10^{-34}$  Js.

OR

- Q4 a) Derive Schrodinger's time independent equation. [6]  
 b) Parameters of three moderator materials are tabulated below: [4]

	$\sigma_s$ (barns)	$\sigma_a$ (barns)	Cost
H <sub>2</sub> O	49.2	0.66	low
D <sub>2</sub> O	10.6	0.001	High
Graphite	4.7	0.0045	moderate

Where,  $\sigma_s$  is scattering cross-section and  $\sigma_a$  is absorption cross-section. On the basis of this information, discuss merits and demerits of these moderator materials.

- c) Calculate binding energy per nucleon for  $U_{92}^{235}$ . Given, mass of  $U^{235}$ , proton and neutron as 235.0439299amu, 1.007276 amu and 1.008665 amu, respectively. [4]

Q.5 Attempt following multiple choice questions:[1x20=20 marks]

- a) Sound waves with frequency > 20kHz is called [1]  
 (i)audible (ii) hypersound  
 (iii) ultrasound (iv) supersonic
- b) Variation of Loudness of sound with its intensity is [1]  
 (i)linear (ii) natural logarithm  
 (iii) exponential (iv) logarithm to the base 10
- c) Ultrasound with high frequency is used in ultrasonic non-destructive testing because smaller wavelength [1]  
 (i)gives better resolution (ii) better collimated beam  
 (iii)cannot be heard by human ear and hence less noise  
 (iv) all of the above
- d) Thickness of a quartz crystal generating ultrasound determines its [1]  
 (i) frequency (ii) speed  
 (iii) intensity (iv) direction
- e) Reverberation time of an auditorium will decrease if [1]  
 (i) chairs in the auditorium are made softer  
 (ii) volume of the auditorium is increased  
 (iii) surface area of the auditorium is decreased  
 (iv) all of the above
- f) A film is said to be thin if its thickness is smaller than [1]  
 (i) wavelength of light (ii) coherence length of light  
 (iii) line width of a spectral line (iv) none of the above

- g) If  $\mu_1$ ,  $\mu$ ,  $\mu_2$  are the refractive indices of air, anti-reflection coating (ARC) and glass, respectively, then the ARC has maximum efficiency if  $\mu =$  [1]
- (i)  $\mu_1\mu_2$  (ii)  $\frac{\mu_1}{\mu_2}$  (iii)  $(\mu_1\mu_2)^{1/2}$  (iv)  $\left(\frac{\mu_1}{\mu_2}\right)^{1/2}$
- h) When monochromatic light with wavelength  $\lambda$  is incident on a slit with width  $a$ , maximum diffraction occurs when [1]
- (i)  $a < \lambda$  (ii)  $a = \lambda$  (iii)  $a > \lambda$  (iv) none of the above
- i) Keeping all other parameters same, if the value of grating element is decreased then grating's [1]
- (i) resolving power decreases (ii) dispersion increases  
(iii) angle of first order spectrum decreases (iv) none of the above
- j) Light from sodium vapour lamp is diffracted using a diffraction grating. Two prominent lines have wavelengths 5890Å and 5896Å. If the angle of diffraction in the first order is  $\theta(5890)$  and  $\theta(5896)$  then [1]
- (i)  $\theta(5890) > \theta(5896)$  (ii)  $\theta(5890) = \theta(5896)$   
(iii)  $\theta(5890) < \theta(5896)$  (iv) none of the above
- k) In an unbiased p-n junction diode [1]
- (i) Intrinsic Fermi energy  $E_{Fi}$  is higher on the p-side than that on the n-side  
(ii) Intrinsic Fermi energy  $E_{Fi}$  is lower on the p-side than that on the n-side  
(iii) Intrinsic Fermi energy  $E_{Fi}$  is equal on the p-side and the n-side  
(iv) none of the above
- l) The barrier potential  $V_{bi}$  in a p-n junction diode depends on [1]
- (i) carrier density in both n-side and p-side  
(ii) band gap of the semiconductor  
(iii) temperature of the diode  
(iv) all of the above
- m) In an n-type semiconductor, the value of  $E_F - E_{Fi}$  increases with [1]
- (i) increase in doping concentration of trivalent impurity  
(ii) increase in doping concentration of pentavalent impurity  
(iii) increase in temperature  
(iv) all of the above



- n) For two samples A and B of n-type semiconductor, the doping concentration of donor impurities is  $1 \times 10^{20} \text{ m}^{-3}$  and  $3 \times 10^{20} \text{ m}^{-3}$ , respectively. If the hole concentration in sample A is  $9 \times 10^{12} \text{ m}^{-3}$ , then the hole concentration in sample B is [1]
- (i)  $3 \times 10^{12} \text{ m}^{-3}$  (ii)  $1 \times 10^{12} \text{ m}^{-3}$  (iii)  $27 \times 10^{12} \text{ m}^{-3}$  (iv)  $9 \times 10^{12} \text{ m}^{-3}$
- o) In an intrinsic semiconductor, the Fermi energy lies at the centre of [1]
- (i) conduction band (ii) valence band  
(iii) forbidden band (iv) covalent bond
- p) Sun light is converted to electrical energy by [1]
- (i) photovoltaic effect (ii) photo-electric effect  
(iii) photo-conductance (iv) photo-luminescence
- q) For a solar PV cell current is equal to  $I_{sc}$  when the load resistance is [1]
- (i) infinite (ii) equal to series resistance of solar cell resistance  
(iii) zero (iv) equal to parallel resistance of solar cell resistance
- r) A solar PV panel is kept at a latitude such that the sun is overhead at 12 noon. Sun beam will go through air mass AM1.2 at an angle of \_\_\_\_\_ w.r.t. vertical [1]
- (i)  $30^\circ$  (ii)  $33.6^\circ$  (iii)  $60^\circ$  (iv)  $67.2^\circ$
- s) Texturing of the surface of solar PV cell is done to [1]
- (i) decrease temperature of solar cell  
(ii) increase light refracted into solar cell  
(iii) increase reflectivity of the surface of solar cell  
(iv) decrease reflectivity of solar cell
- t) If the band gap of the solar cell material is 1.44 then it will not absorb light of wavelength [1]
- (i)  $4000 \text{ \AA}$  (ii)  $6000 \text{ \AA}$  (iii)  $8000 \text{ \AA}$  (iv)  $9000 \text{ \AA}$